

# Eugene Yakimov

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

312  
papers

2,299  
citations

23  
h-index

32  
g-index

321  
ext. papers

2,556  
ext. citations

1.7  
avg, IF

5.29  
L-index

#	Paper	IF	Citations
312	Communication Electron-Beam Stimulated Release of Dislocations from Pinning Sites in GaN. <i>ECS Journal of Solid State Science and Technology</i> , <b>2022</b> , 11, 015003	2	
311	GaAs diodes for TiT-based betavoltaic cells. <i>Applied Radiation and Isotopes</i> , <b>2022</b> , 179, 110030	1.7	3
310	Betavoltaic cell based on Ni/ $\beta$ -Ga <sub>2</sub> O <sub>3</sub> and <sup>63</sup> Ni source. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2022</b> , 40, 010401	2.9	1
309	Deep level defect states in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> and e-Ga <sub>2</sub> O <sub>3</sub> crystals and films: Impact on device performance. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2022</b> , 40, 020804	2.9	11
308	Cathodoluminescence and EBIC investigations of stacking fault expansion in 4H-SiC due to e-beam irradiation at fixed points. <i>Journal Physics D: Applied Physics</i> , <b>2022</b> , 55, 245101	3	0
307	Electrical properties of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> films grown by halide vapor phase epitaxy on sapphire with $\beta$ -Cr <sub>2</sub> O <sub>3</sub> buffers. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 215701	2.5	1
306	Structural and electrical properties of thick $\beta$ -Ga <sub>2</sub> O <sub>3</sub> grown on GaN/sapphire templates. <i>APL Materials</i> , <b>2022</b> , 10, 061102	5.7	1
305	Effect of Compressive and Stretching Strains on the Dislocation Luminescence Spectrum in Silicon. <i>Semiconductors</i> , <b>2021</b> , 55, 633	0.7	1
304	1 GeV proton damage in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> . <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 185701	2.5	1
303	Investigation of the Effect of Irradiation by a Low-Energy Electron Beam on the Capacitance-Voltage Characteristics of SiO <sub>2</sub> . <i>Journal of Surface Investigation</i> , <b>2021</b> , 15, 1045-1048	0.5	
302	Parasitic p-n junctions formed at V-pit defects in p-GaN. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 155702	2.5	1
301	Experimental estimation of electron-hole pair creation energy in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2021</b> , 118, 202106	3.4	8
300	Electrical properties and deep trap spectra in Ga <sub>2</sub> O <sub>3</sub> films grown by halide vapor phase epitaxy on p-type diamond substrates. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 185701	2.5	6
299	Grown and Characterization of ZnO Aligned Nanorod Arrays for Sensor Applications. <i>Energies</i> , <b>2021</b> , 14, 3750	3.1	1
298	Estimations of Activation Energy for Dislocation Mobility in p-GaN. <i>ECS Journal of Solid State Science and Technology</i> , <b>2021</b> , 10, 026004	2	1
297	Study of Wide-Gap Semiconductors Using Electron-Beam Induced Current Method. <i>Crystallography Reports</i> , <b>2021</b> , 66, 581-593	0.6	4
296	On the nature of photosensitivity gain in Ga <sub>2</sub> O <sub>3</sub> Schottky diode detectors: Effects of hole trapping by deep acceptors. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 879, 160394	5.7	6

295	Dislocations introduced in n-GaN at room temperature cause conductivity inversion. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 877, 160281	5.7	2
294	Effect of Electron-Beam Irradiation on the Cathodoluminescence of a ZnO Nanorod Array. <i>Journal of Surface Investigation</i> , <b>2021</b> , 15, 1208-1211	0.5	0
293	Influence of the Structural Parameters of Triple Junctions of Special Grain Boundaries on Their Recombination Activity. <i>Journal of Surface Investigation</i> , <b>2021</b> , 15, S1-S6	0.5	
292	Photosensitivity of Ga <sub>2</sub> O <sub>3</sub> Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , <b>2020</b> , 8, 111105	5.7	13
291	Radiation-enhanced dislocation glide in 4H-SiC at low temperatures. <i>Journal of Alloys and Compounds</i> , <b>2020</b> , 837, 155470	5.7	1
290	Study of single-layer stacking faults in 4H-SiC by deep level transient spectroscopy. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 172101	3.4	3
289	Electron-Beam Domain Patterning in Sr <sub>0.61</sub> Ba <sub>0.39</sub> Nb <sub>2</sub> O <sub>6</sub> Crystals. <i>Coatings</i> , <b>2020</b> , 10, 299	2.9	2
288	Charging Effects in Al-SiO <sub>2</sub> -p-Si Structures After Low-Energy Electron Beam Irradiation. <i>Journal of Electronic Materials</i> , <b>2020</b> , 49, 5178-5183	1.9	3
287	Pulsed fast reactor neutron irradiation effects in Si doped n-type $\beta$ -Ga <sub>2</sub> O <sub>3</sub> . <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 274001	3	13
286	Editors' Choice Electrical Properties and Deep Traps in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> :Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 045003	2	10
285	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 495108	3	11
284	Comparative Study of Optical and Electrical Properties of Grown-In and Freshly Introduced Dislocations in GaN by SEM Methods. <i>Journal of Electronic Materials</i> , <b>2020</b> , 49, 5173-5177	1.9	1
283	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochochalski $\beta$ -Ga <sub>2</sub> O <sub>3</sub> (Mg). <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, Q3019-Q3023	2	25
282	Defect structure and properties of Zn diffusion doped Si after swift Xe ion irradiation. <i>Journal of Physics: Conference Series</i> , <b>2019</b> , 1190, 012011	0.3	
281	Defects at the surface of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> produced by Ar plasma exposure. <i>APL Materials</i> , <b>2019</b> , 7, 061102	5.7	25
280	Simulation of the Properties of Betavoltaic Cells Based on Silicon and <sup>63</sup> Ni Enriched Film. <i>Journal of Surface Investigation</i> , <b>2019</b> , 13, 285-288	0.5	
279	Annealing and LEEBI Effects on the Stacking Fault Expansion and Shrinking in 4H-SiC. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900151	1.6	3
278	New functional material: spark plasma sintered Si/SiO nanoparticles - fabrication and properties.. <i>RSC Advances</i> , <b>2019</b> , 9, 16746-16753	3.7	0

277	Estimations of Low Temperature Dislocation Mobility in GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900163	1.6	3
276	Thermoresistive Semiconductor SiC/Si Composite Material. <i>Semiconductors</i> , <b>2019</b> , 53, 220-223	0.7	2
275	Effect of Nickel and Copper Introduced at Room Temperature on the Recombination Properties of Extended Defects in Silicon. <i>Semiconductors</i> , <b>2019</b> , 53, 411-414	0.7	2
274	Deep trap spectra of Sn-doped $\beta$ -Ga <sub>2</sub> O <sub>3</sub> grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , <b>2019</b> , 7, 051103	5.7	22
273	Dependence of the Bulk Electrical Properties of Multisilicon on the Grain Misorientation Parameters. <i>Semiconductors</i> , <b>2019</b> , 53, 55-59	0.7	
272	Simulation of the Parameters of a Titanium-Tritide-Based Beta-Voltaic Cell. <i>Semiconductors</i> , <b>2019</b> , 53, 96-98	0.7	1
271	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Doped with Fe. <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, Q3091-Q3096	2	19
270	Deep traps and persistent photocapacitance in $\beta$ -(Al <sub>0.14</sub> Ga <sub>0.86</sub> ) <sub>2</sub> O <sub>3</sub> /Ga <sub>2</sub> O <sub>3</sub> heterojunctions. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 095702	2.5	1
269	Hydrogen plasma treatment of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 032101	3.4	29
268	Room-Temperature Ni Interaction with Deformation-Induced Defects in Si: A DLTS Study. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900326	1.6	3
267	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> . <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, P661-P666	2	4
266	Crystal structure, vibrational spectroscopy and optical properties of a one-dimensional organic-inorganic hybrid perovskite of [NH <sub>2</sub> CH <sub>2</sub> CH(NH <sub>2</sub> )CH <sub>2</sub> ] <sub>2</sub> BiCl. <i>Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials</i> , <b>2019</b> , 75, 880-886	1.8	11
265	Metal Impurities and Gettering in Crystalline Silicon <b>2019</b> , 1-46		
264	Metal Impurities and Gettering in Crystalline Silicon <b>2019</b> , 495-540		1
263	Recombination and optical properties of dislocations gliding at room temperature in GaN under applied stress. <i>Journal of Alloys and Compounds</i> , <b>2019</b> , 776, 181-186	5.7	12
262	Electrical Activity of Extended Defects in Multicrystalline Silicon. <i>Semiconductors</i> , <b>2018</b> , 52, 254-259	0.7	3
261	Betavoltaic battery performance: Comparison of modeling and experiment. <i>Applied Radiation and Isotopes</i> , <b>2018</b> , 137, 184-189	1.7	21
260	Point defect induced degradation of electrical properties of Ga <sub>2</sub> O <sub>3</sub> by 10 MeV proton damage. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 032107	3.4	72

259	Temperature Dependence of Low-Energy Electron Beam Irradiation Effect on Optical Properties of MQW InGaN/GaN Structures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700646	1.3	2
258	Some new insights into the impact of annealing on single stacking faults in 4H-SiC. <i>Superlattices and Microstructures</i> , <b>2018</b> , 120, 7-14	2.8	6
257	Quantum Barrier Growth Temperature Affects Deep Traps Spectra of InGaN Blue Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , <b>2018</b> , 7, Q80-Q84	2	7
256	Diffusion length of non-equilibrium minority charge carriers in $\text{InGa}_{2}\text{O}_3$ measured by electron beam induced current. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 185704	2.5	37
255	Photoluminescence mapping of GaN epilayers with different degrees of order of mosaic structure <b>2018</b> , 333-336		
254	SEM investigations of individual extended defects in GaN epilayers <b>2018</b> , 597-600		
253	Recombination properties of dislocations in GaN. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 161543	2.5	21
252	Structural investigation of light-emitting A3B5 structures grown on Ge/Si(100) substrate. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 1124, 022037	0.3	1
251	Investigation of the Effect of Electron-Beam Irradiation on the Defect Structure of Laterally Overgrown GaN Films via the Induced-Current and Cathodoluminescence Methods. <i>Journal of Surface Investigation</i> , <b>2018</b> , 12, 994-999	0.5	
250	Estimation of the Maximum Nonequilibrium Charge-Carrier Concentration in GaN Under Electron-Beam Irradiation. <i>Journal of Surface Investigation</i> , <b>2018</b> , 12, 1000-1004	0.5	2
249	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated $\text{InGa}_{2}\text{O}_3$ . <i>Applied Physics Letters</i> , <b>2018</b> , 113, 092102	3.4	46
248	Structural and optical characteristics of GaAs films grown on Si/Ge substrates. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 993, 012014	0.3	1
247	Development of betavoltaic cell technology production based on microchannel silicon and its electrical parameters evaluation. <i>Applied Radiation and Isotopes</i> , <b>2017</b> , 121, 71-75	1.7	8
246	Structural, electrical and luminescent characteristics of ultraviolet light emitting structures grown by hydride vapor phase epitaxy. <i>Modern Electronic Materials</i> , <b>2017</b> , 3, 32-39	0.3	
245	Defects responsible for lifetime degradation in electron irradiated n-GaN grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 112102	3.4	21
244	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 115704	2.5	19
243	Low temperature stacking fault nucleation and expansion from stress concentrators in 4H-SiC. <i>Acta Materialia</i> , <b>2017</b> , 139, 155-162	8.4	7
242	Investigation of stacking faults introduced into 4H-SiC crystals by indentation. <i>Journal of Surface Investigation</i> , <b>2017</b> , 11, 234-237	0.5	2

241	Comparative study of the spectral and structural properties of EuAl <sub>3</sub> (BO <sub>3</sub> ) <sub>4</sub> single crystals with different morphologies. <i>Physics of the Solid State</i> , <b>2017</b> , 59, 2423-2429	0.8	
240	Study of Low Voltage Prebreakdown Sites in Multicrystalline Si Based Cells by the LBIC, EL, and EDS Methods. <i>Advances in Condensed Matter Physics</i> , <b>2017</b> , 2017, 1-5	1	2
239	Contactless mapping of electrical properties inhomogeneities by the surface electron beam induced voltage method <b>2017</b> , 75-78		
238	Reconstruction of electrical properties distribution around extended defects with submicron spatial resolution based on the SEM-EBIC measurement <b>2017</b> , 79-82		
237	Electron beam induced excess carrier concentration. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2017</b> , 14, 1600266		6
236	Dislocation trails in Si: Geometry and electrical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2017</b> , 14, 1700074		5
235	Recombination Processes in 4H-SiC pn Structures. <i>Materials Science Forum</i> , <b>2016</b> , 858, 345-348	0.4	1
234	Deep Electron Traps Responsible for Higher Quantum Efficiency in Improved GaN/InGaN Light Emitting Diodes Embedded with SiO <sub>2</sub> Nanoparticles. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q274-Q277	2	13
233	Dislocation glide in GaN films grown by the lateral-overgrowth method induced by low-energy electron-beam irradiation. <i>Journal of Surface Investigation</i> , <b>2016</b> , 10, 959-961	0.5	2
232	Physical properties of carbon films obtained by methane pyrolysis in an electric field. <i>Technical Physics</i> , <b>2016</b> , 61, 428-431	0.5	1
231	Effect of low energy electron beam irradiation on Shockley partial dislocations bounding stacking faults introduced by plastic deformation in 4H-SiC in its brittle temperature range. <i>Superlattices and Microstructures</i> , <b>2016</b> , 99, 226-230	2.8	11
230	Extended defect study in Si: EBIC versus LBIC. <i>Superlattices and Microstructures</i> , <b>2016</b> , 99, 202-207	2.8	3
229	Radiation enhanced basal plane dislocation glide in GaN. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FM03	1.4	9
228	Deep traps determining the non-radiative lifetime and defect band yellow luminescence in n-GaN. <i>Journal of Alloys and Compounds</i> , <b>2016</b> , 686, 1044-1052	5.7	24
227	Heterostructure optimization for increasing LED efficiency. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FJ13	1.4	10
226	Diffusion length measurements in GaN. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FH04	1.4	14
225	Electrical, luminescent, and deep trap properties of Si doped n-GaN grown by pendeo epitaxy. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 015103	2.5	23
224	Studies of deep level centers determining the diffusion length in epitaxial layers and crystals of undoped n-GaN. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 205109	2.5	23

223	Prediction of betavoltaic battery output parameters based on SEM measurements and Monte Carlo simulation. <i>Applied Radiation and Isotopes</i> , <b>2016</b> , 112, 98-102	1.7	11
222	Diffusion length and grain boundary recombination activity determination by means of induced current methods. <i>Superlattices and Microstructures</i> , <b>2016</b> , 99, 108-112	2.8	1
221	Electrical, Luminescent and Structural Properties of Nanopillar GaN/InGaN Multi-Quantum-Well Structures Prepared by Dry Etching. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q165-Q170	1.7	8
220	Development and investigation of silicon converter beta radiation <sup>63</sup> Ni isotope. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2016</b> , 110, 012029	0.4	4
219	Electron traps as major recombination centers in n-GaN films grown by metalorganic chemical vapor deposition. <i>Applied Physics Express</i> , <b>2016</b> , 9, 061002	2.4	13
218	Recombination activity of interfaces in multicrystalline silicon. <i>Semiconductors</i> , <b>2015</b> , 49, 724-728	0.7	6
217	MBE-grown AlGaIn/GaN heterostructures for UV photodetectors. <i>Technical Physics</i> , <b>2015</b> , 60, 546-552	0.5	3
216	Study of the properties of silicon-based semiconductor converters for betavoltaic cells. <i>Semiconductors</i> , <b>2015</b> , 49, 746-748	0.7	12
215	Quantitative description of the properties of extended defects in silicon by means of electron- and laser-beam-induced currents. <i>Semiconductors</i> , <b>2015</b> , 49, 741-745	0.7	2
214	Indium doping-induced change in the photoconduction spectra of o-TaS <sub>3</sub> . <i>Physica B: Condensed Matter</i> , <b>2015</b> , 460, 180-184	2.8	3
213	Effect of low-energy electron irradiation on the optical properties of structures containing multiple InGaIn/GaN quantum well. <i>Semiconductors</i> , <b>2015</b> , 49, 143-148	0.7	4
212	Minority carrier diffusion length in Al <sub>x</sub> Ga <sub>1-x</sub> N (x = 0.1) grown by ammonia molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2015</b> , 12, 447-450		2
211	Movement of basal plane dislocations in GaN during electron beam irradiation. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 132101	3.4	19
210	Characterization of 4H-SiC pn Structures with Unstable Excess Current. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 648-651	0.4	
209	Spatial Distribution of the Dislocation Trails in Silicon. <i>Solid State Phenomena</i> , <b>2015</b> , 242, 155-159	0.4	5
208	Investigation of nitride films by the electron-beam-induced current method. <i>Journal of Surface Investigation</i> , <b>2015</b> , 9, 939-943	0.5	4
207	Characterization of Si Convertors of Beta-Radiation in the Scanning Electron Microscope. <i>Solid State Phenomena</i> , <b>2015</b> , 242, 312-315	0.4	6
206	Photoluminescence enhancement by localized surface plasmons in AlGaIn/GaN/AlGaIn double heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2015</b> , 9, 575-579	2.5	4

205	EBIC and LBIC investigations of dislocation trails in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2015</b> , 12, 1081-1084		5
204	EBIC investigations of dislocations in ELOG GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2015</b> , 12, 1132-1135		5
203	Effect of copper on the recombination activity of extended defects in silicon. <i>Semiconductors</i> , <b>2015</b> , 49, 716-719	0.7	3
202	EBIC and LBIC studies of the properties of extended defects in plastically deformed silicon. <i>Semiconductors</i> , <b>2015</b> , 49, 720-723	0.7	3
201	Inverse bias effect on the optical properties of light-emitting diodes with multiple InGaN/GaN quantum wells when irradiated by an electron beam in a scanning electron microscope. <i>Journal of Surface Investigation</i> , <b>2015</b> , 9, 944-947	0.5	1
200	Increase in the diffusion length of minority carriers in Al <sub>x</sub> Ga <sub>1-x</sub> N alloys (x = 0.1) fabricated by ammonia molecular beam epitaxy. <i>Semiconductors</i> , <b>2015</b> , 49, 1285-1289	0.7	5
199	What is the real value of diffusion length in GaN?. <i>Journal of Alloys and Compounds</i> , <b>2015</b> , 627, 344-351	5.7	58
198	Studying stacking faults in SiC by the XBIC method using a laboratory X-ray source. <i>Journal of Surface Investigation</i> , <b>2014</b> , 8, 155-157	0.5	1
197	Comparison of the efficiency of <sup>63</sup> Ni beta-radiation detectors made from silicon and wide-gap semiconductors. <i>Journal of Surface Investigation</i> , <b>2014</b> , 8, 843-845	0.5	13
196	Electrical, optical, and structural properties of GaN films prepared by hydride vapor phase epitaxy. <i>Journal of Alloys and Compounds</i> , <b>2014</b> , 617, 200-206	5.7	10
195	DEEP TRAPS SPECTRA IN UNDOPED GAN FILMS GROWN BY HYDRIDE VAPOR PHASE EPITAXY UNDER VARIOUS CONDITIONS. <i>American Journal of Applied Sciences</i> , <b>2014</b> , 11, 1714-1721	0.8	1
194	Electrical and optical properties of stacking faults introduced by plastic deformation in 4H-SiC <b>2014</b> ,		3
193	Low energy electron beam irradiation effect on optical properties of nanopillar MQW InGaN/GaN structures <b>2014</b> ,		1
192	Structural defects responsible for excessive leakage current in Schottky diodes prepared on undoped n-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 051212	1.3	4
191	Microcathodoluminescence spectra evolution for planar and nanopillar multi-quantum-well GaN-based structures as a function of electron irradiation dose. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 011207	1.3	7
190	Defect detection in solar cells via electroluminescence, LBIC, and EBIC methods. <i>Journal of Surface Investigation</i> , <b>2014</b> , 8, 839-842	0.5	4
189	XBIC using a laboratory X-ray source. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2013</b> , 77, 21-23	0.4	1
188	Application of a scanning electron microscope in simulating a beta-emission-induced current. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 81-84	0.5	7



187	Investigation of stacking faults in 4H-SiC using the electron-beam-induced current method. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 856-858	0.5	1
186	Rate of generation of nonequilibrium charge carriers by a focused X-ray beam. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 859-862	0.5	2
185	Temperature dependence of the cathodoluminescence spectra of irradiated light-emitting-diode structures with multiple InGaN/GaN quantum wells. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 844-847	0.5	1
184	Simulation of the current induced by <sup>63</sup> Ni beta radiation. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 852-855	0.5	12
183	Properties of nanopillar structures prepared by dry etching of undoped GaN grown by maskless epitaxial overgrowth. <i>Journal of Alloys and Compounds</i> , <b>2013</b> , 554, 258-263	5.7	9
182	Analysis of the temperature dependence of the capacitance-voltage characteristics of InGaN/GaN multiple quantum well light-emitting structures. <i>Semiconductors</i> , <b>2013</b> , 47, 162-168	0.7	5
181	Influence of metal impurities on recombination activity of dislocations in multicrystalline silicon. <i>Semiconductors</i> , <b>2013</b> , 47, 232-234	0.7	6
180	Cathodoluminescence and electron beam induced current investigations of stacking faults mechanically introduced in 4H-SiC in the brittle domain. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 084903	2.5	12
179	Low energy electron irradiation effect on optical and electrical properties of InGaN/GaN multiple quantum well structures. <i>International Journal of Nanoparticles</i> , <b>2013</b> , 6, 191	0.4	4
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173	Effect of contamination with iron on the electron-beam-induced current contrast of extended defects in multicrystalline silicon. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 897-900	0.5	2
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161	Frequency and temperature dependences of capacitance-voltage characteristics of InGaIn/GaN light-emitting structures with multiple quantum wells. <i>Semiconductors</i> , <b>2011</b> , 45, 221-224	0.7	7
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147	EBIC study of nonradiative recombination in silicon LEDs with near-band-edge luminescence. <i>Semiconductors</i> , <b>2010</b> , 44, 1241-1243	0.7	
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143	Effect of dislocation trails on gold diffusion in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 1823-1826		4
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132	Influence of extended defects on gold diffusion in plastically deformed silicon. <i>Journal of Surface Investigation</i> , <b>2009</b> , 3, 608-611	0.5	2
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117	Simulation and measurements of EBIC images of photoconductive elements based on HgCdTe. <i>Semiconductors</i> , <b>2007</b> , 41, 407-410	0.7	2
116	EBIC measurements of small diffusion length in semiconductor structures. <i>Semiconductors</i> , <b>2007</b> , 41, 411-413	0.7	46

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93	Correlation of diffusion length and trap concentration with dislocation density in MOCVD-grown GaN. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 479-483	2.8	4
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36	Temperature dependence of dislocation efficiency as sinks for self-interstitials in silicon as measured by gold diffusion. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 1495-1499	2.5	25
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34	Increase of Electrical Activity of Dislocations in Si during Plastic Deformation. <i>Materials Science Forum</i> , <b>1995</b> , 196-201, 1183-1188	0.4	2
33	Effect of dislocation loop size on the deep level transient spectrum in Si. <i>Physica Status Solidi A</i> , <b>1994</b> , 143, K5-K7		5
32	Modulated electron-beam-induced current and cathodoluminescence. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1994</b> , 24, 23-27	3.1	3
31	Modulated cathodoluminescence for extended defect characterization. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1994</b> , 24, 121-123	3.1	3
30	Processes of Defect Formation and Gettering under Dry Etching of Si and GaAs and Measurements of Diffusion Length Profile. <i>Solid State Phenomena</i> , <b>1993</b> , 32-33, 99-104	0.4	
29	Effect of Deep Level Athermal Recharging on DLTS Spectra in HgCdTe. <i>Physica Status Solidi A</i> , <b>1993</b> , 136, 455-463		1
28	Possibilities of modulated cathodoluminescence for multilayer structure characterization. <i>Scanning</i> , <b>1993</b> , 15, 31-36	1.6	6
27	SEM Characterization of Multilayer Structures. <i>Acta Physica Polonica A</i> , <b>1993</b> , 83, 81-86	0.6	2
26	Mapping of diffusion length and depletion region width in Schottky diodes. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, A171-A174	1.8	4

25	Spatial distribution of dislocation-related centers in plastically deformed silicon. <i>Physica Status Solidi A</i> , <b>1991</b> , 127, 67-73		7
24	EBIC-Investigation of the Dislocation-Impurity Interaction in Silicon. <i>Solid State Phenomena</i> , <b>1991</b> , 1-2, 59-63	0.4	3
23	Electrical Properties of Dislocation Impurity Atmospheres in Si. <i>Solid State Phenomena</i> , <b>1991</b> , 19-20, 367-372		7
22	Scanning deep level transient spectroscopy (SDLTS) investigations of deep level spatial distribution in implanted silicon. <i>Journal of Crystal Growth</i> , <b>1990</b> , 103, 287-290	1.6	1
21	SEM investigation of semiconductors by the capacitance techniques. <i>Microelectronic Engineering</i> , <b>1990</b> , 12, 179-185	2.5	7
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19	EBIC Investigation of the Electrical Activity of Dislocations with Different Impurity Atmospheres in Si. <i>Physica Status Solidi A</i> , <b>1990</b> , 122, 121-128		20
18	Potential relief in PbTe:In(Cd) heterophase systems. <i>Journal of Physics and Chemistry of Solids</i> , <b>1990</b> , 51, 1333-1338	3.9	4
17	Microtomography of semiconductor crystals in the EBIC mode. <i>Journal of Crystal Growth</i> , <b>1990</b> , 103, 197-199		2
16	EFFECT OF DISLOCATIONS ON THE LOCAL ELECTRICAL PROPERTIES OF N-SI <b>1990</b> , 1443-1446		3
15	Plasma Stimulated Impurity Redistribution in Silicon. <i>Physica Status Solidi A</i> , <b>1989</b> , 111, 81-88		13
14	SEM-EBIC investigations of grain boundaries in cadmium telluride. <i>Physica Status Solidi A</i> , <b>1988</b> , 109, K3-K6		2
13	Scanning electron microscopy in submicron structure diagnostics. <i>Vacuum</i> , <b>1988</b> , 38, 1045-1050	3.7	8
12	Dislocation-Impurity Interaction and its Effect on Semiconductor Properties. <i>Materials Research Society Symposia Proceedings</i> , <b>1988</b> , 138, 173		9
11	Electrical Properties and Defect Structure of Plastically Deformed Silicon Crystals Doped with Gold. <i>Physica Status Solidi A</i> , <b>1987</b> , 102, 687-695		9
10	Photoluminescence of Preannealed Plastically Deformed Silicon Crystals. <i>Physica Status Solidi A</i> , <b>1986</b> , 93, K143-K146		2
9	Recombination properties of dislocation slip planes. <i>Physica Status Solidi A</i> , <b>1986</b> , 95, 173-177		27
8	The Electrical Activity of Dislocation Slip Planes in Semiconductor Crystals. <i>Materials Science Forum</i> , <b>1986</b> , 10-12, 787-790	0.4	8

7	Asymmetry of isolated dislocation mobility in Silicon single crystals. <i>Crystal Research and Technology</i> , <b>1984</b> , 19, 295-302	1.3	12
6	The EBIC contrast of dislocation slip planes in silicon. <i>Physica Status Solidi A</i> , <b>1984</b> , 84, K43-K45		2
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4	ASYMMETRY OF ISOLATED DISLOCATIONS MOBILITY IN Ge AND Si SINGLE CRYSTALS. <i>Journal De Physique Colloque</i> , <b>1983</b> , 44, C4-85-C4-89		2
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1	Electron-Beam-Induced Current and Deep-Level Transient Spectroscopy Study of Dislocation Trails in Au-Doped Si. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2100095	1.6	